

1. Scope :

This specification applies to ambient light photo diode chips,
Device No. PD-50120C-B

2. Structure :

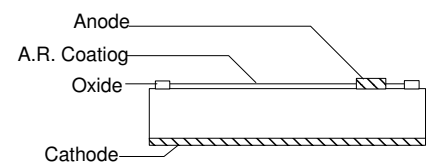
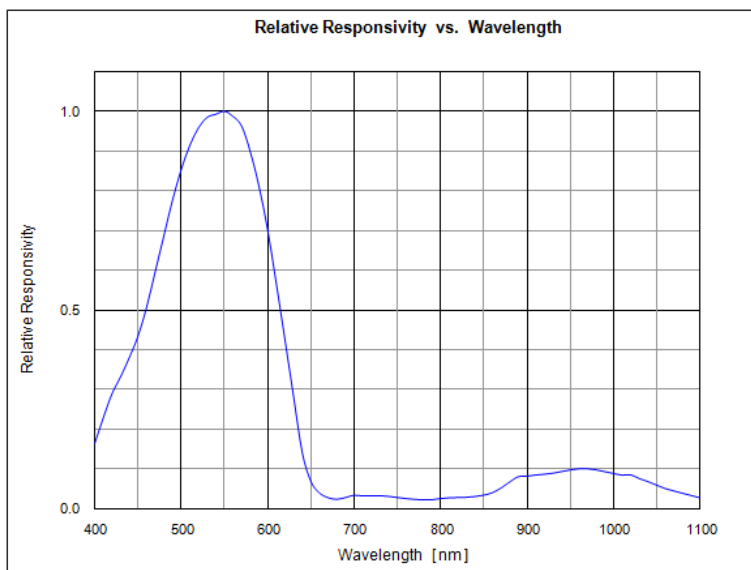
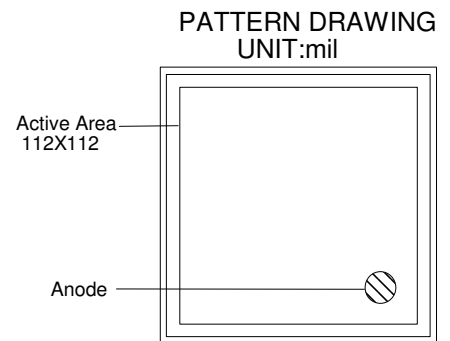
- 2-1. Planar type : P/N diode.
- 2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold.

3. Size :

- 3-1. Chip size : 125 mils × 125 mils (3.175 mm × 3.175 mm).
- 3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038 mm).
- 3-3. Active area : 112 mils × 112 mils (2.840 mm × 2.840 mm).
- 3-4. Bonding pad (Anode) : 8 mils (0.200mm) Diameter.
- 3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 °C)

| Parameter | Symbol | Condition | Min. | Typ. | Max. | Unit |
|---------------------------|-------------|----------------------------------|------|------|------|------|
| Reverse dark Current | I_D | $V_R=10V$ $E_e=0mW/cm^2$ | | | 30 | nA |
| Reverse breakdown voltage | $V_{(BR)R}$ | $I_R=100\mu A$ $E_e=0mW/cm^2$ | 30 | | | V |
| * Spectral Response | λ_p | --- | | 550 | | nm |



* bare chip measured